

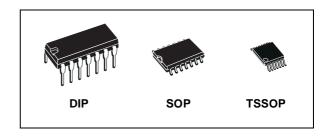


8-INPUT NOR/OR GATE

- HIGH SPEED:
 - t_{PD} = 10ns (TYP.) at V_{CC} = 6V
- LOW POWER DISSIPATION: $I_{CC} = 1\mu A(MAX.)$ at $T_A=25^{\circ}C$
- HIGH NOISE IMMUNITY: V_{NIH} = V_{NIL} = 28 % V_{CC} (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE: |I_{OH}| = I_{OL} = 4mA (MIN)
- BALANCED PROPAGATION DELAYS: t_{PLH} ≅ t_{PHL}
- WIDE OPERATING VOLTAGE RANGE: V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 4078



The M74HC4078 is an high speed CMOS 8-INPUT NOR/OR GATE fabricated with silicon gate C^2 MOS technology.

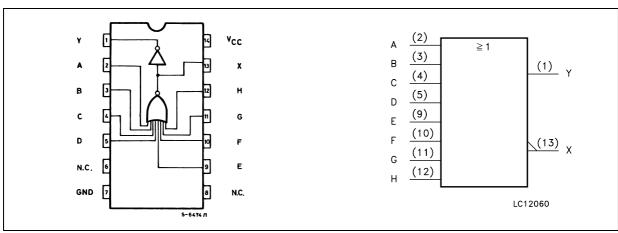


ORDER CODES

PACKAGE	TUBE	T & R
DIP	M74HC4078B1R	
SOP	M74HC4078M1R	M74HC4078RM13TR
TSSOP		M74HC4078TTR

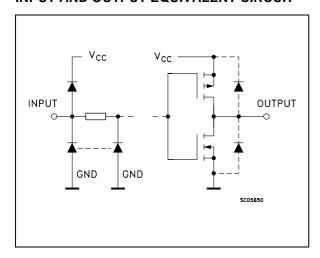
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



July 2001 1/8

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
2, 3, 4, 5, 9, 10, 11, 12	A to H	Data Inputs
1, 13	Y, X	Data Outputs
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

TRUTH TABLE

INPUTS	OUTI	PUTS
INFOIS	x x	
ALL INPUTS "L"	Н	L
OTHER POSSIBILITIES	L	Н

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
Io	DC Output Current	± 25	mA
I_{CC} or I_{GND}	DC V _{CC} or Ground Current	± 50	mA
P_{D}	Power Dissipation	500(*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
V _{CC}	Supply Voltage		2 to 6	V
V _I	Input Voltage		0 to V _{CC}	V
Vo	Output Voltage		0 to V _{CC}	V
T _{op}	Operating Temperature		-55 to 125	°C
	Input Rise and Fall Time	V _{CC} = 2.0V	0 to 1000	ns
t_r, t_f		$V_{CC} = 4.5V$	0 to 500	ns
		$V_{CC} = 6.0V$	0 to 400	ns

DC SPECIFICATIONS

		1	Test Condition				Value				
Symbol	bol Parameter		V _{CC}		T _A = 25°C			-40 to 85°C		-55 to 125°C	
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input	2.0		1.5			1.5		1.5		
	Voltage	4.5		3.15			3.15		3.15		V
		6.0		4.2			4.2		4.2		
V_{IL}	Low Level Input	2.0				0.5		0.5		0.5	
	Voltage	4.5				1.35		1.35		1.35	V
		6.0				1.8		1.8		1.8	
V_{OH}	High Level Output	2.0	I _O =-20 μA	1.9	2.0		1.9		1.9		
	Voltage	4.5	I _O =-20 μA	4.4	4.5		4.4		4.4		
		6.0	I _O =-20 μA	5.9	6.0		5.9		5.9		V
		4.5	I _O =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0	I _O =-5.2 mA	5.68	5.8		5.63		5.60		
V _{OL}	Low Level Output	2.0	I _O =20 μA		0.0	0.1		0.1		0.1	
	Voltage	4.5	I _O =20 μA		0.0	0.1		0.1		0.1	
		6.0	I _O =20 μA		0.0	0.1		0.1		0.1	V
		4.5	I _O =4.0 mA		0.17	0.26		0.33		0.40	
		6.0	I _O =5.2 mA		0.18	0.26		0.33		0.40	
I _I	Input Leakage Current	6.0	$V_I = V_{CC}$ or GND			± 0.1		± 1		± 1	μΑ
Icc	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND			1		10		20	μΑ

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ns}$)

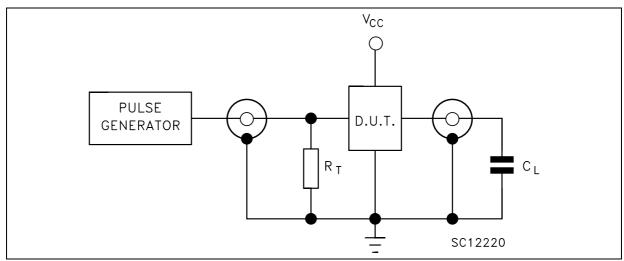
		1	est Condition	Value							
Symbol	Parameter	V _{CC}		Т	A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		V _{CC}		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{TLH} t _{THL}	Output Transition	2.0			30	75		95		110	
	Time	4.5			8	15		19		22	ns
		6.0			7	13		16		19	
t _{PLH} t _{PHL}	Propagation Delay	2.0			48	95		120		145	
	Time	4.5			12	19		24		29	ns
		6.0			10	16		20		25	

CAPACITIVE CHARACTERISTICS

		1	est Condition				Value				
Symbol	Parameter	v _{cc}		T,	_A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C _{IN}	Input Capacitance	5.0			5	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)	5.0			37						pF

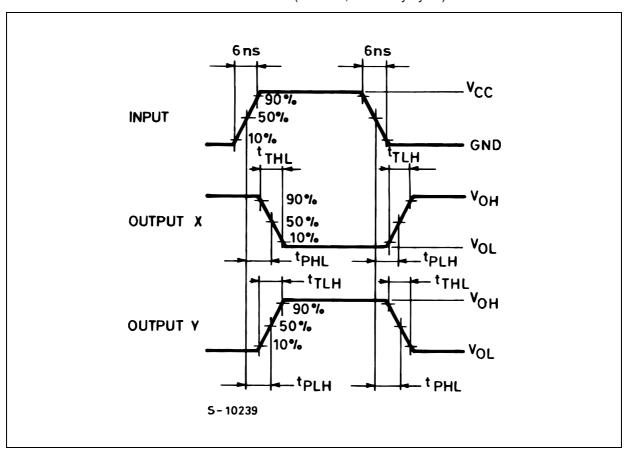
¹⁾ C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I_{CC(opr)} = C_{PD} x V_{CC} x f_{IN} + I_{CC} 4

TEST CIRCUIT



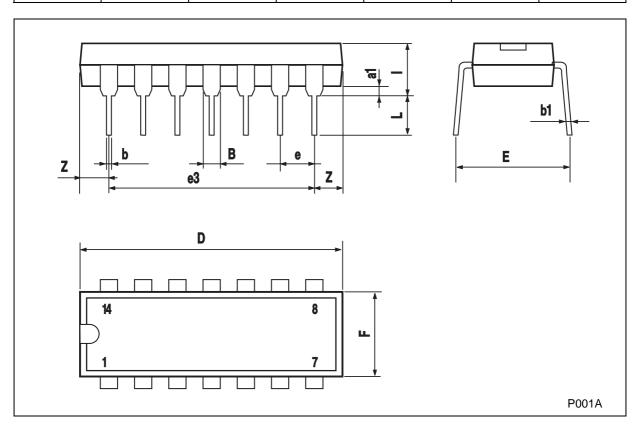
 C_L = 50pF or equivalent (includes jig and probe capacitance) R_T = Z_{OUT} of pulse generator (typically 50 Ω)

WAVEFORM: PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)



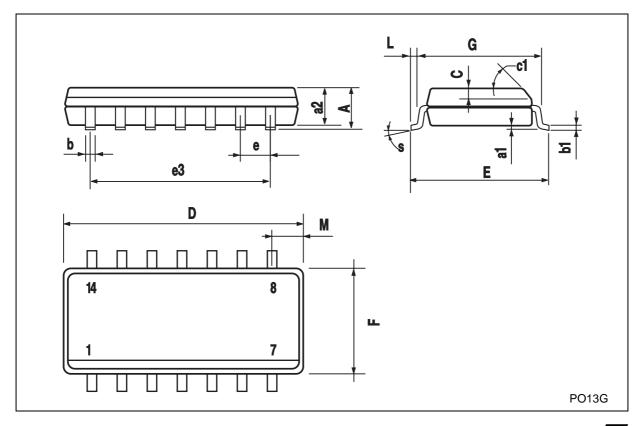
Plastic DIP-14 MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
е		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



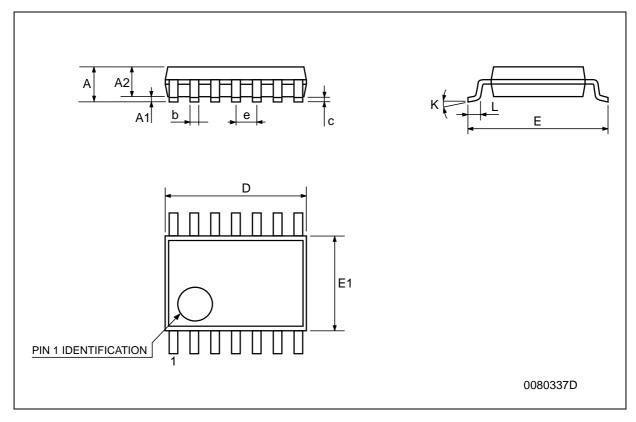
SO-14 MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.019	
c1			45°	(typ.)	•	
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
М			0.68			0.026
S		!	8° (r	nax.)	•	!



TSSOP14 MECHANICAL DATA

DIM.		mm.			inch	
DIIVI.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.
Α			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
С	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
Е	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
е		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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